## CHEM2DMAC

## Interlayer excitons in van-der-Waals heterostructures: MoS<sub>2</sub> on GaSe

**Christian Wagner<sup>1,2</sup>,** M. Rahaman<sup>1</sup>, D.R.T. Zahn<sup>1</sup> and S. Gemming<sup>1,2</sup> <sup>1</sup>Helmholtz-Zentrum Dresden-Rossendorf, Bautzner Landstraße 400, 01328 Dresden, Germany <sup>2</sup>Chemnitz University of Technology, Institut für Physik, Reichenhainer Str. 70, 09127 Chemnitz c.wagner@hzdr.de

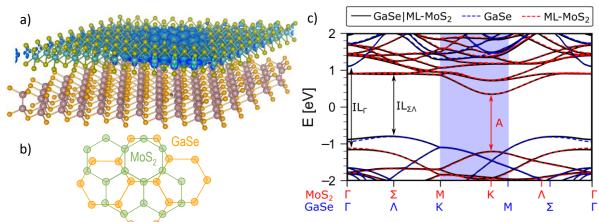
Hybrid van-der-Waals heterostructures of two-dimensional nanomaterials are a vibrant field of study: The (weak) electronic interaction between two layers is often reasonably described by a perturbation of the physical effects of the isolated layers, such as electrostatic doping and increased screening of *intralayer* excitons. However, it turns out that this picture of the weak interaction is not exhaustive in terms of all optical properties: the formation of *interlayer* excitons. These mixed states are measured experimentally by photoluminescence and photocurrents and predicted by theory. Examples are of MoS<sub>2</sub> or MoSe<sub>2</sub> on WSe<sub>2</sub>, MoS<sub>2</sub> or GaSe due to type-II band alignment [1-3]. The conditions for the formation of interlayer excitons are elucidated from a first-principles point of view. For this, first-principles studies of a minimal test system of MoS<sub>2</sub> on GaSe is conducted [1]. This work envisions to predict the interlayer states as a function of the heterostack in order to

specifically tailor efficient photon absorption.

## References

- [1] M. Rahaman, C. Wagner et al., J. Phys.: Condens. Matter 31, 114001 (2019).
- [2] H. Fang, C. Battaglia et al., PNAS 111, 6198 (2014).
- [3] P. Rivera, J. R. Schaibley et al., Nat. Commun. 6, 6242 (2015).

## **Figures**



**Figure 1:** a) The  $MoS_2$  | GaSe bilayer and the hole exciton wave function for the interlayer exciton at  $\Lambda$ . b) Both materials form a nearly commensurate superlattice at a rotation angle of 30°. c) The band structure of the bilayer system compared to the band structure of the individual layers: The  $MoS_2$  layer is polarized by the proximity of the GaSe layer. As a consequence, the conduction band edge of GaSe is higher in energy than the one of  $MoS_2$  (type-II alignment) and additional GaSe valence band states appear within the band gaps of the pristine  $MoS_2$ .